

## Features

-30V, -3A,  $R_{DS(ON)} = 120m\Omega @ V_{GS} = -10V$   
Fast switching  
Green Device Available  
Suit for -4.5V Gate Drive Applications

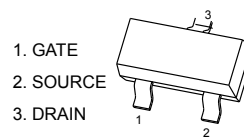
$V_{DSS}$  -30 V  
 $I_D$  -3 A  
 $R_{DS(ON)}$  120m $\Omega$

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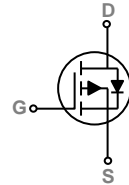
## Applications

Notebook  
Load Switch  
Battery Protection  
Hand-held Instruments

### SOT-23



### Equivalent Circuit



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

**Absolute Maximum Ratings** (@  $T_C = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_A = 25^\circ\text{C}$ )	-3.0	A
	Drain Current – Continuous ( $T_A = 70^\circ\text{C}$ )	-0.21	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	-10	A
$P_D$	Power Dissipation ( $T_A = 25^\circ\text{C}$ )	1.3	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.012	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	$^\circ\text{C}/\text{W}$

## Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ unless otherwise noted)

### Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^{\circ}\text{C}, I_D=-1\text{mA}$	---	-0.02	---	$\text{V}/^{\circ}\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-30V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	-1	$\mu A$
		$V_{DS}=-24V, V_{GS}=0V, T_J=75^{\circ}\text{C}$	---	---	-10	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA

### On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-2.8A$	---	---	120	m $\Omega$
		$V_{GS}=-4.5V, I_D=-2.0A$	---	---	170	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-2.8	---	$\text{mV}/^{\circ}\text{C}$
gfs	Forward Transconductance	$V_{DS}=-10V, I_D=-1A$	---	3	---	S

### Dynamic and switching Characteristics

$Q_g$	Total Gate Charge <sup>2,3</sup>	$V_{DS}=-24V, V_{GS}=-4.5V, I_D=-2A$	---	2.5	---	nC
$Q_{gs}$	Gate-Source Charge <sup>2,3</sup>		---	0.1	---	
$Q_{gd}$	Gate-Drain Charge <sup>2,3</sup>		---	1.8	---	
$T_{d(on)}$	Turn-On Delay Time <sup>2,3</sup>	$V_{DD}=-15V, V_{GS}=-10V, R_G=6\Omega$ $I_D=-1A$	---	6.1	---	ns
$T_r$	Rise Time <sup>2,3</sup>		---	8.7	---	
$T_{d(off)}$	Turn-Off Delay Time <sup>2,3</sup>		---	33.2	---	
$T_f$	Fall Time <sup>2,3</sup>		---	3.7	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, F=1\text{MHz}$	---	240	---	pF
$C_{oss}$	Output Capacitance		---	40	---	
$C_{rss}$	Reverse Transfer Capacitance		---	28	---	
$R_g$	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	9.5	---	$\Omega$

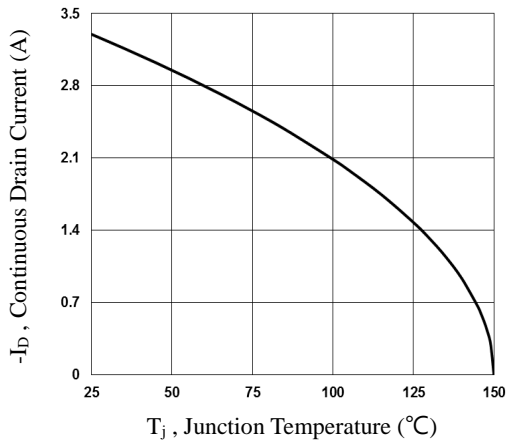
### Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	-3.0	A
$I_{SM}$	Pulsed Source Current		---	---	-6.0	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^{\circ}\text{C}$	---	---	-1.2	V

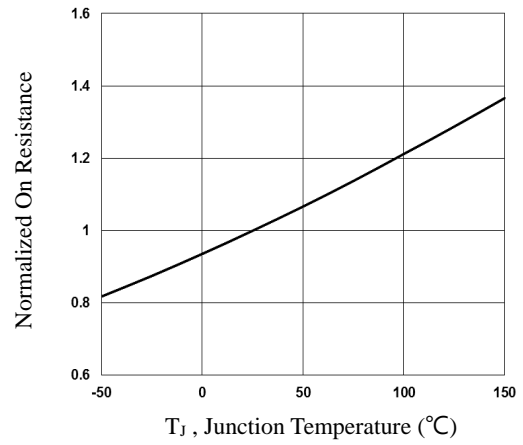
Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$ .
3. Essentially independent of operating temperature.

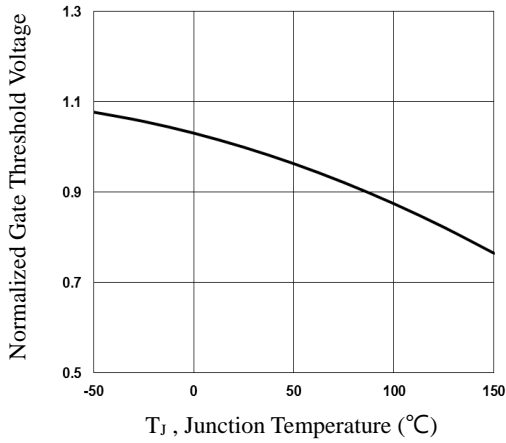
**RATING AND CHARACTERISTIC CURVES**



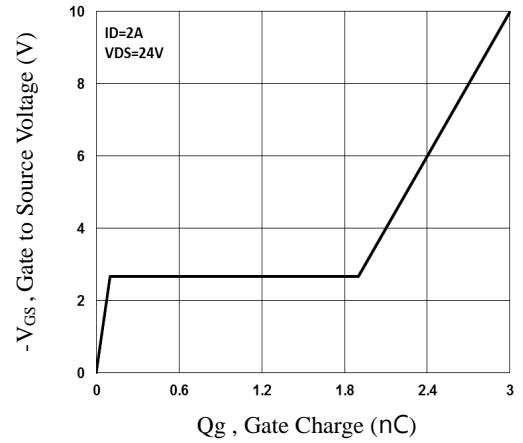
**Fig.1 Continuous Drain Current vs.  $T_c$**



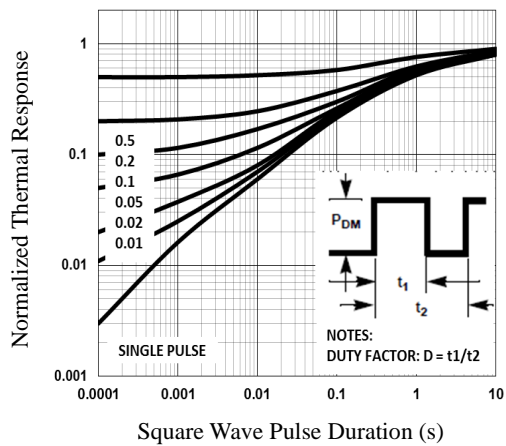
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$**



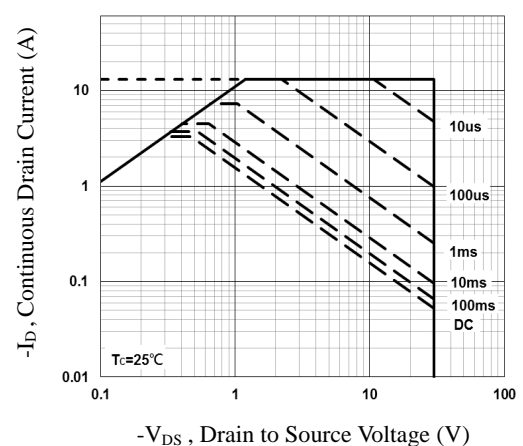
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



**Fig.4 Gate Charge Waveform**

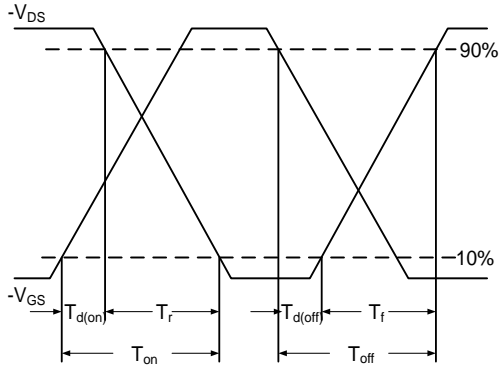


**Fig.5 Normalized Transient Impedance**

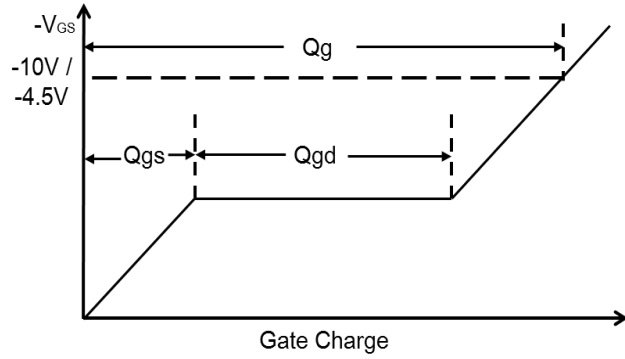


**Fig.6 Maximum Safe Operation Area**

RATING AND CHARACTERISTIC CURVES



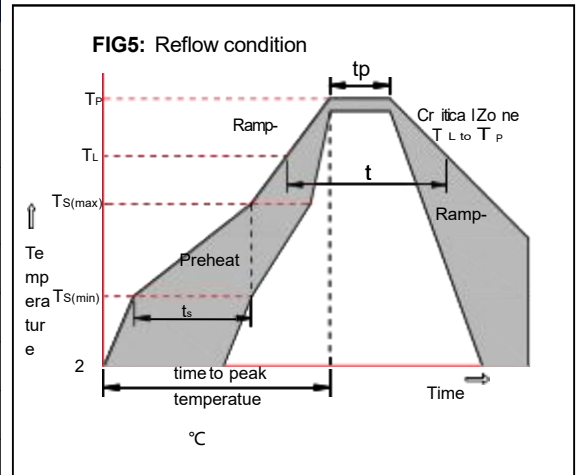
**Fig.7 Switching Time Waveform**



**Fig.8 Gate Charge Waveform**

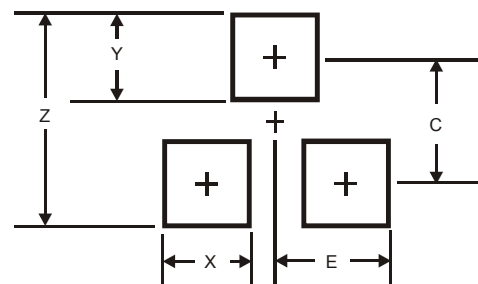
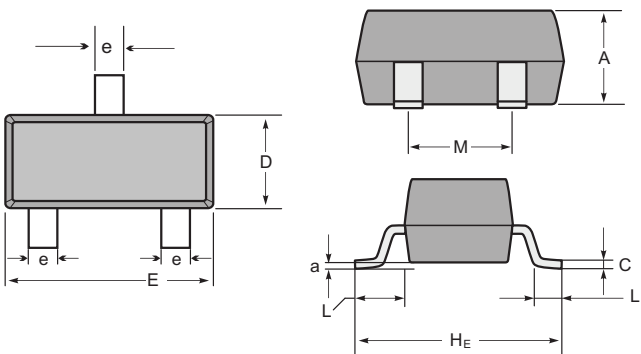
**Soldering parameters**

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150°C
	-Temperature Max( $T_{s(max)}$ )	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp ( $T_L$ ) to peak)		3°C/sec. Max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature( $T_L$ )(Liquid us)	+217°C
	-Temperature( $t_L$ )	60-150 secs.
Peak Temp ( $T_P$ )		+260(+0/-5)°C
Time within 5°C of actual Peak Temp ( $t_p$ )		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp ( $T_P$ )		8 min. Max
Do not exceed		+260°C



**Package Dimensions & Suggested Pad Layout**

**SOT23**



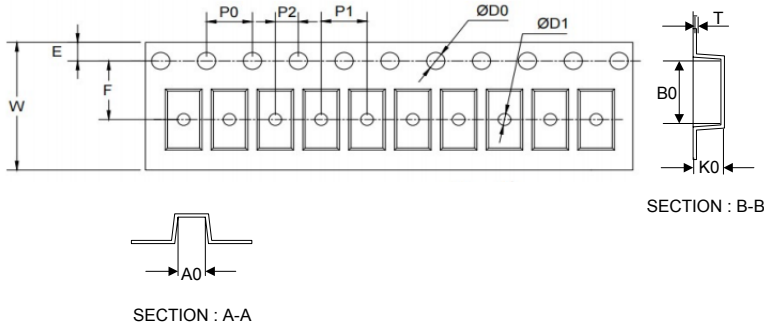
**SOT-23 mechanical data**

UNIT	A	C	D	E	$H_e$	e	M	L	$L_1$	a	
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
<b>Z</b>	2.9
<b>X</b>	0.8
<b>Y</b>	0.9
<b>C</b>	2.0
<b>E</b>	1.35

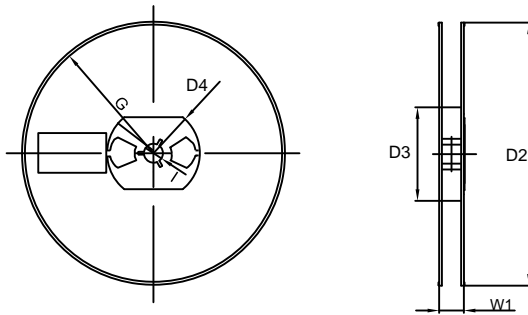
Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.10
P1	4.00±0.10
P2	2.00±0.10
D0	1.55±0.10
D1	1.05±0.10
E	1.55±0.10
F	3.60±0.10
W	8.00±0.10
A0	3.80±0.20
B0	3.25±0.20
K0	1.45±0.10
T	0.25±0.05
D2	178.0±3.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0

7" Reel



Quantity: 3000PCS